

REMARKS

Favorable reconsideration of this application, as amended, is respectfully requested.

The claims have been amended, where appropriate, to distinguish patentably from Yang et al., relied upon in the rejection under 35 U.S.C. § 102(e).

The manner in which the claims distinguish patentably from Yang et al. will now be described, but the references to the drawings and the specification of the present application are for ease in explaining features of the claims, as examples, and are not intended to limit the scope of the claims.

Claim 1 recites, inter alia, a connection portion (CNP in Fig. 1) for an active region that partially connects first and second active regions (100-1 and 100-2 in Fig. 10) adjacent with each other with a device isolation region put therebetween in a first direction where control gates (110) extend in the memory cell array. Yang et al. do not disclose this feature.

An adjacent direction of the first active region and the second active region pointed out in the rejection is not a direction in which control gates extend, but is perpendicular to that direction. If the first active region under BL1 and the second active region under BL2 (in Fig. 3)

is considered, and moreover, the connection portion SL1 (in Fig. 3) is considered, there is not a contact hole to SL1 for an active region that partially connects first and second active regions. Yang et al. merely disclose that each contact hole (BL1 or BL2 in Fig. 4) exists in each active region (under BL1 or BL2 in Fig. 3 and Fig. 5).

In contrast to Yang et al, in the invention recited in Claim 1, there is a contact hole for connecting a global bit line (103) to the connection portion for an active region that partially connects first and second active regions adjacent with each other with a device isolation region put therebetween in a first direction in which control gates in the memory cell array extend (Fig. 6). Accordingly, there is a common contact hole (108) for connecting the first active region (100) and the second active region (100 in Fig. 1). Therefore, it is possible to decrease the number of contacts holes and global bit lines and to decrease the chip area.

As recited in Claim 2, the gate of the first transistor and the gate of the second transistor are disposed without overlap thereof along the first direction. Therefore, it is possible to decrease the area for the first and second selection transistor portions (104). See Fig. 6 and page 10, line 19 to page 11, line 2.

Claim 12 recites, inter alia, memory cells each having a first gate, a second gate, and a third gate different in the function from the first gate and the second gate, in which two active regions adjacent to each other with the device isolation region put therebetween in a first direction in which control gates extend are combined in one set, and respective active regions are connected by way of contact holes to a global line in common. This invention is not disclosed by Yang et al.

Accordingly, Claims 1 and 12 and the claims dependent thereon should be allowed.

New independent Claim 16 recites, inter alia, that a gate of the first selection transistor and a gate of the second selection transistor are disposed without overlap thereof along a first direction, in which a control gate extends in a memory cell region, and a second direction perpendicular to the first direction. The inventions of Claim 16 and of dependent Claim 17 are not disclosed by Yang et al. Accordingly, these claims should be allowed also.

The Commissioner is hereby authorized to charge to Deposit Account No. 50-1165 any fees under 37 C.F.R. §§ 1.16 and 1.17 that may be required by this paper and to credit any overpayment to that Account. If any extension of time is required in connection with the filing of this paper and

has not been requested separately, such extension is hereby requested.

Respectfully submitted,

NHS:lmb

Miles & Stockbridge P.C.
1751 Pinnacle Drive
Suite 500
McLean, Virginia 22102
(703) 903-9000

By: Nelson H. Shapiro
Nelson H. Shapiro
Reg. No. 17,095

February 28, 2005